

ABSTRACT OF THE DISCLOSURE

A semiconductor laser device as one example of semiconductor light-emitting devices includes a semiconductor laser chip and a submount serving respectively as a semiconductor light-emitting device chip and a mount member, the semiconductor laser chip including a GaN substrate and a stack. The semiconductor laser chip is bonded to a mount surface of the submount by means of solder, with the stack facing the mount surface. The submount includes a material having a higher thermal expansion coefficient than GaN which is a material for the GaN substrate.

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